

AMENDMENT TO THE CLAIMS

Claim 1 (currently amended) A programmable resistance memory element, comprising:

- a first dielectric material having a sidewall surface;
- a conductive layer formed over said sidewall surface;
- a second dielectric material formed over said conductive layer, wherein an edge of said conductive layer is exposed;
- a third dielectric material formed over said edge, said third dielectric material having a an opening formed therethrough uncovering a portion of said edge; and
- a programmable resistance material disposed in said opening and in communication with said edge.

Claim 2 (original) The memory element of claim 1, wherein said opening has a lateral dimension less than a photolithographic limit.

Claim 3 (original) The memory element of claim 1, wherein said opening is a trench.

Claim 4 (original) The memory element of claim 1, wherein said edge is annular.

Claim 5 (original) The memory element of claim 1, wherein said edge is linear.

Claim 6 (original) The memory element of claim 1, wherein said conductive layer is a sidewall layer.

Claim 7 (original) The memory element of claim 1, wherein said conductive layer is a sidewall spacer or liner.

Claim 8 (original) The memory element of claim 1, wherein said memory material is a phase-change material.

Claim 9 (original) The memory element of claim 1, wherein said memory material comprises a chalcogen element.

Claims 10-21 (canceled)